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NO. 1976 --P. 6--

Form PTO-1449

U.S. Department of Commerce
Patent and Trademark OfficeAttorney Docket No.
5308-231 DVSerial No.
To Be AssignedLIST OF DOCUMENTS CITED BY APPLICANT
(Use several sheets if necessary)Applicants:
David B. Slater, Jr. et al.Filing Date:
To Be Assigned

GAU 11/23/05

U.S. PATENT DOCUMENTS

Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing Date Appropriation
II	1	6,229,160	05/08/01	Krames et al.	257	94	
II	2	6,222,207	04/24/01	Carter-Coman et al.	257	98	
II	3	6,204,523	03/20/01	Carey et al.	257	98	
II	4	6,201,264	03/13/01	Khare et al.	257	97	
II	5	6,194,742	02/27/01	Kern et al.	257	94	
II	6	6,177,688	01/23/01	Linthicum et al.	257	77	
II	7	6,169,294	01/02/01	Biing-Jye et al.	257	79	
II	8	6,147,458	11/14/00	Bucks et al.	325	225	
II	9	6,139,166	10/31/00	Marshall et al.	362	231	
II	10	6,133,589	10/17/00	Krames et al.	257	103	
II	11	6,121,637	09/19/00	Isokawa et al.	257	99	
II	12	6,121,636	09/19/00	Morita et al.	257	99	
II	13	6,118,259	09/12/00	Bucks et al.	323	312	
II	14	6,097,041	08/01/00	Lin et al.	257	98	
II	15	6,091,085	07/18/00	Lester	257	98	
II	16	6,046,465	04/04/00	Wang et al.	257	98	
II	17	5,952,681	09/14/99	Chen	257	89	
II	18	5,917,202	06/29/99	Haltz et al.	257	98	
II	19	5,912,477	06/15/99	Negley	257	95	
II	20	5,779,924	07/14/98	Krames et al.	216	24	
II	21	5,777,350	07/07/98	Nakamura et al.	257	96	
II	22	5,767,581	06/16/98	Nakamura et al.	257	749	
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II	24	5,523,589	06/04/96	Edmond et al.	257	77	
II	25	5,416,342	05/16/95	Edmond et al.	257	76	
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II	27	5,369,289	11/29/94	Tamaki et al.	257	99	
II	28	5,247,533	09/21/93	Okazaki et al.	372	45	
II	29	5,237,182	08/17/93	Kitagawa et al.	257	15	
II	30	5,210,031	05/11/93	Carter, Jr.	437	107	
II	31	5,187,547	02/16/93	Niina et al.	257	77	
II	32	5,087,949	02/11/92	Haltz	357	17	
II	33	5,006,908	04/09/91	Matsuoka et al.	357	17	
II	34	4,966,862	10/30/90	Edmond	437	100	

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		Document Number	Date	Country	Class	Subclass	Translation Yes / No
II	35	GB 2 346 480 A	08/09/00	United Kingdom			
II	36	2000-195827	07/14/00	Japan			X (Abstract)
II	37	EP 0 961 328 A2	12/01/99	EPO			
II	38	10-256604	09/25/98	Japan			X (Abstract)
II	39	10-233549	09/02/98	Japan			X (Abstract)
II	40	10-163530	06/19/98	Japan			X (Abstract)
II	41	09-223846	08/26/97	Japan			X (Abstract)
II	42	9-82587	03/28/97	Japan			X (Abstract)
II	43	08-321660	12/03/96	Japan			X (Abstract)
II	44	07-235729	09/05/95	Japan			X (Abstract)
II	45	06-232510	08/19/94	Japan			X (Abstract)
II	46	1-223377	09/08/89	Japan			X (Abstract)
II	47	56-131977	10/15/81	Japan			X (Abstract)

Examiner:

Date Considered:

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Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5308-231	Serial No. To Be Assigned
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: David B. Slater, Jr., et al.	
				Filing Date: To Be Assigned	
				GAU:	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
TT	48	OSRAM Enhances Brightness of Blue InGaN LEDs, Compound Semiconductor, Volume 7, No. 1, February 2001, p. 7			
TT	49	Craford, Outlook for AllInGaP Technology, Presentation, Strategies in Light 2000			
TT	50	Krames et al., High-Power Truncated-Inverted-Pyramid (Al _{0.5} Ga _{0.5} In _{0.5} P/GaP Light-Emitting Diodes Exhibiting > 50% External Quantum Efficiency, Applied Physics Letters, Vol. 75, No. 16, October 18, 1999, pp. 2365-2367			
TT	51	Lambrecht et al., Band Structure Interpretation of the Optical Transitions Between Low-Lying Conduction Bands in n-Type Doped SiC Polytypes, Materials Science Forum, Vols. 264-268, 1998, pp. 271-274			
TT	52	Craford, Overview of Device Issues in High-Brightness Light-Emitting Diodes, Chapter 2, High Brightness Light Emitting Diodes: Semiconductors and Semimetals, Vol. 48, Stringfellow et al. ed., Academic Press, 1997, pp. 47-63			
TT	53	Yoo et al., Bulk Crystal Growth of 6H-SiC on Polytype-Controlled Substrates Through Vapor Phase and Characterization, Journal of Crystal Growth, Vol. 115, Vol. 1991, pp. 733-739			
TT	54	Biederman, The Optical Absorption Bands and Their Anisotropy in the Various Modifications of SiC, Solid State Communications, Vol. 3, 1965, pp. 343-346			
TT	55	U.S. Application Serial No. 09/154,363, entitled Vertical Geometry InGaN LED			

Examiner:

Date Considered:

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Substitute form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	1
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OCT 07 2002

PATENT & TRADE

Application Number

Filing Date

First Named Inventor

Group Art Unit

Examiner Name

Attorney Docket Number

Date if Known

~~10/200,244~~ TO BE ASSIGNED

July 22 2002 CONCURRENTLY

David B. Slater, Jr.

~~2844~~

Unknown

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Examiner Signature

Date Considered

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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet: 1

of

PATENT & TRADEMARK

Application Number	6200-244 TO BE ASSIGNED
Filing Date	07/23/2002 CONCURRENTLY
First Named Inventor	David B. Slater, Jr.
Group Art Unit	2023
Examiner Name	Tan N. Tran
Attorney Docket Number	6308-231 DV

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code (if known)			
TT	1.	2003/0008418	A1	Emerson et al.	01/09/2003	
TT	2.	6,455,878	B1	Bhat et al.	09/24/2002	
TT	3.	6,187,806	B1	Edmond et al.	02/13/2001	
TT	4.	6,120,600		Edmond et al.	09/18/2000	
TT	5.	5,739,554		Edmond et al.	04/14/1998	
TT	6.	5,631,190		Negley	05/20/1997	
TT	7.	5,604,135		Edmond et al.	02/18/1997	
TT	8.	5,338,994		Lazan et al.	08/18/1994	
TT	9.	5,027,168		Edmond	06/26/1991	
TT	10.	4,918,497		Edmond	04/17/1990	

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Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Office	Number	Kind Code (if known)				
TT	11.	JP	11-191841	A	Matsushita Electron Corp.	07/13/1999		
TT	12.	EP	0 051 172	A1	Siemens Aktiengesellschaft	03/12/1982		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
TT	13.	International Search Report, PCT/US02/02849, 12/02/02	
TT	14.	U.S. Application Serial No. 10/003,331, filed 10/31/01, Low Temperature Formation of Backside Ohmic Contacts for Vertical Devices	
TT	15.	U.S. Application Serial No. 60,411,880, filed 09/19/02, Phosphor-Coated Light Emitting Diodes Including Tapered Sidewalls, and Fabrication Methods	
TT	16.	U.S. Application Serial No. 60,307,235, filed 07/23/01, Light Emitting Diodes Including Modifications for Light Extraction and Manufacturing Methods Therefor	
TT	17.	U.S. Application Serial No. 60/294,445, filed 05/30/01, Multi-Quantum Well Light Emitting Diode Structure	
TT	18.	U.S. Application Serial No. 60/294,378, filed 05/30/01, Light Emitting Diode Structure With Multi-Quantum Well and Superlattice Structure	
TT	19.	U.S. Application Serial No. 60/294,308, filed 05/30/01, Light Emitting Diode Structure With Superlattice Structure	
TT	20.	U.S. Application Serial No. 09/787,189, filed 03/15/01, Low Temperature Formation of Backside Ohmic Contacts for Vertical Devices	
TT	21.	U.S. Application Serial No. 60/289,707, filed 02/01/01, Light Emitting Diode With Optically Transparent Silicon Carbide Substrate	
TT	22.	Menz et al., In _x Ga _{1-x} N/Al _x Ga _{1-x} N Violet Light Emitting Diodes With Reflective p-Contacts for High Single Sided Light Extraction, Electronics Letters, Vol. 33, No. 24, 11/20/97, pp. 2088-2089	
TT	23.	Honma et al., Evaluation of Barrier Metals of Solder Bumps for Flip-Chip Interconnection, Electronic Manufacturing Technology Symposium, 1995, Proceedings of 1995 Japan International, 18 th IEEE/CPMT, 12/04/95, pp. 113-116	
TT	24.	Lee et al., Bonding of InP Laser Diodes by Au-Sn Solder and Tungsten-Based Barrier Metallization Schemes, Semiconductor Science and Technology, Vol. 9, No. 4, 4/94, pp. 379-385	


Examiner Signature	<i>Tan N. Tran</i>	Date Considered	06/16/03
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Substitute form 1449A/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	36200241 TO BE ASSIGNED	
			Filing Date	07/22/2002 CONCURRENTLY	
			First Named Inventor	David B. Slater, Jr.	
			Group Art Unit	2629	
			Examiner Name	Tan N. Tran	
Sheet	1	of	1	Attorney Docket Number	5308-231 DV

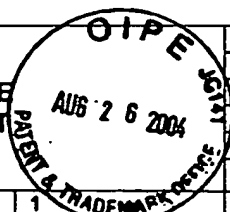
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OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	†
TI	7	International Search Report, PCT/US02/23268, 05/22/2003	

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Substitute form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/825,647
		Filing Date	04/15/2004
		First Named Inventor	David B. Slater, Jr.
		Group Art Unit	Unassigned
		Examiner Name	Unassigned
Sheet 1 of 1	Attorney Docket Number	5308-231DV	



U.S. PATENTS AND PATENT PUBLICATIONS					
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
REP	1	US-2004/0149999	A1	Uemura et al.	08/05/2004
REP	2	US-4,441,187		Bouley et al.	04/03/1984
REP	3	US-4,238,764		Carballes et al.	12/09/1980
REP	4	US-3,894,919		Schwartz et al.	07/15/1975
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			
REP	5	WO	03/010817	A2	Cree, Inc.	02/06/2003	
REP	6	WO	02/101841	A1	Toyoda Gosei Co., Ltd.	12/19/2002	
REP	7	WO	02/075819	A2	Osram Opto Semiconductors GMBH & Co., OHG	09/26/2002	
REP	8	WO	01/47039	A1	Lumileds Lighting, U.S., LLC	06/28/2001	
REP	9	JP	2001-291899	A	Sanken Electric Co Ltd.	10/19/2001	
REP	10	JP	11-340514	A	Nichia Chem Ind Ltd	12/10/1999	
REP	11	JP	11-121803	A	Hitachi Cable Ltd	04/30/1999	

OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
REP	12	International Search Report, PCT/US03/21909, 08/10/2004	

Examiner Signature		Date Considered	1/4/06
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